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TRIPLE COLOR LED LAMPS

Pb
Lead-Free Parts

LRGB3392-C

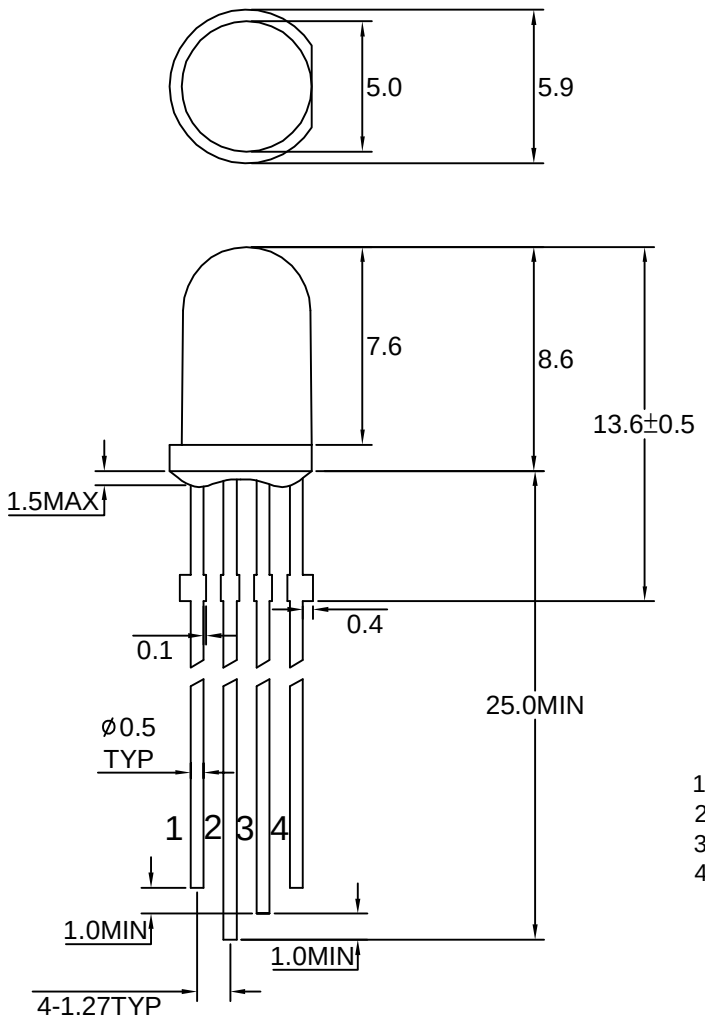
DATA SHEET

DOC. NO : QW0905-LRGB3392-C

REV. : A

DATE : 17 - Jan - 2008

Package Dimensions



1.ANODE RED
2.COMMON CATHODE
3.ANODE BLUE
4.ANODE GREEN

Note : 1.All dimension are in millimeter tolerance is ±0.25mm unless otherwise noted.
2.Specifications are subject to change without notice.

Absolute Maximum Ratings at Ta=25 ℃

Parameter	Symbol	Absolute Maximum Ratings			**UNIT**
		URF	DGM	DBK	
Forward Current	IF	50	30	30	mA
Peak Forward Current Duty 1/10@10KHz	IFP	130	100	100	mA
Power Dissipation	PD	120	120	120	mW
Reverse Current @5V	Ir	10	50	50	μA
Electrostatic Discharge	ESD	2000	1000	1000	V
Operating Temperature	Topr	-20 ~ +80			℃
Storage Temperature	Tstg	-30 ~ +100			℃

Typical Electrical & Optical Characteristics (Ta=25 ℃)

PART NO	MATERIAL	COLOR		Peak wave length λ Pnm	Dominant wave length λ Dnm	Spectral halfwidth △λ nm	Forward voltage @20mA(V)			Luminous intensity @20mA(mcd)		Viewing angle 2θ 1/2 (deg)
		Emitted	Lens				Min.	Typ.	Max.	Min.	Typ.	
LRGB3392-C	AlGaInP	Red	White Diffused	----	630	20	1.5	----	2.4	450	700	40
	InGaN/GaN	Green		518	525	36	----	3.5	4.0	700	1100	50
	InGaN/GaN	Blue		----	470	30	----	3.5	4.0	160	300	50

Note : 1.The forward voltage data did not including ±0.1V testing tolerance.
2. The luminous intensity data did not including ±15% testing tolerance.

Typical Electro-Optical Characteristics Curve

URF CHIP

Fig.1 Forward current vs. Forward Voltage

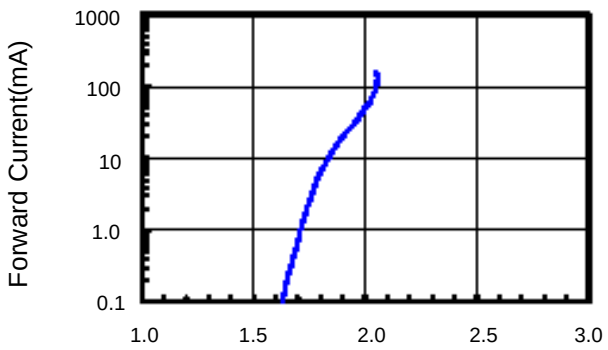


Fig.2 Relative Intensity vs. Forward Current

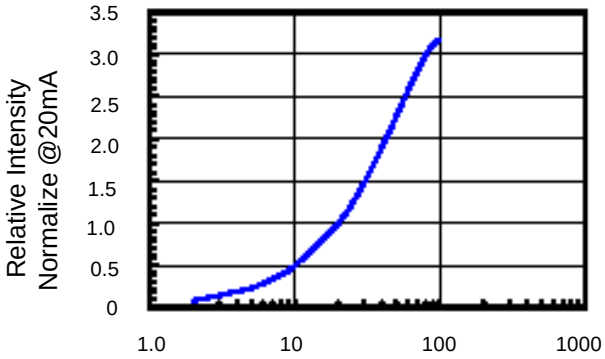


Fig.3 Forward Voltage vs. Temperature

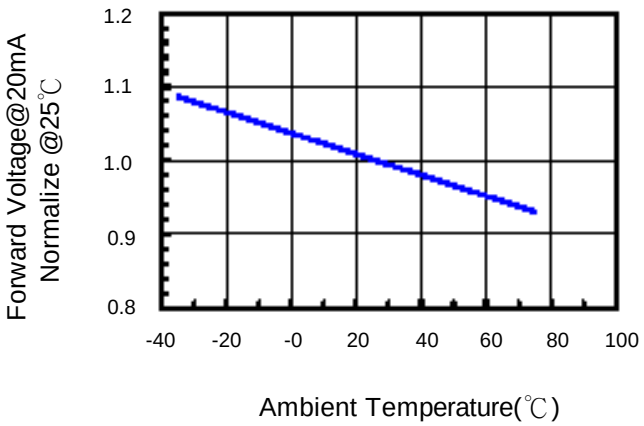


Fig.4 Relative Intensity vs. Temperature

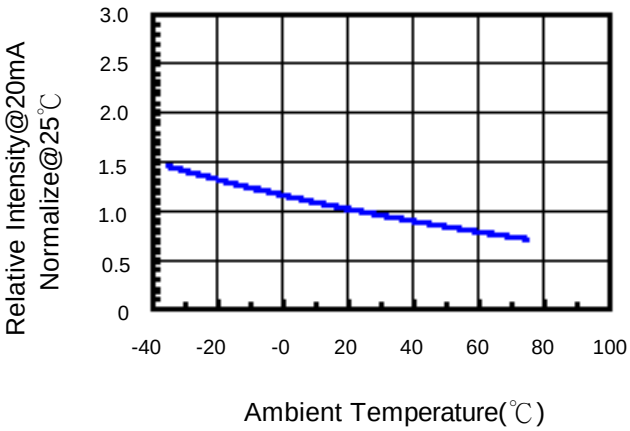


Fig.5 Relative Intensity vs. Wavelength

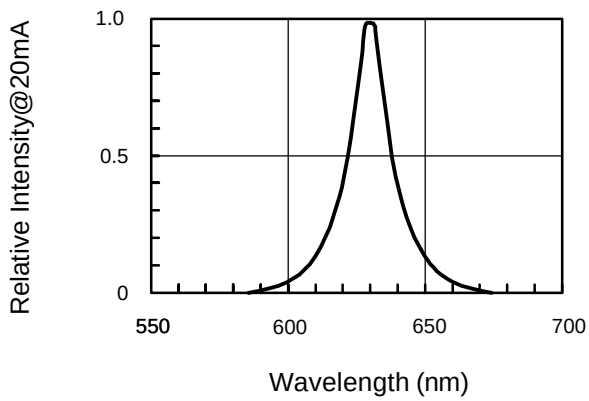
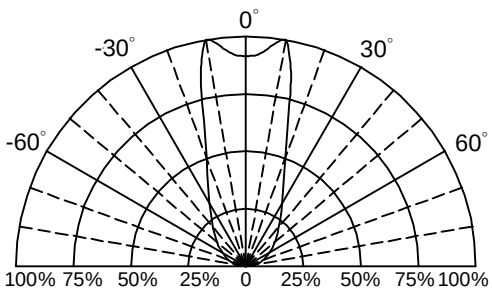


Fig.6 Directive Radiation



Typical Electro-Optical Characteristics Curve

DGM CHIP

Fig.1 Forward current vs. Forward Voltage

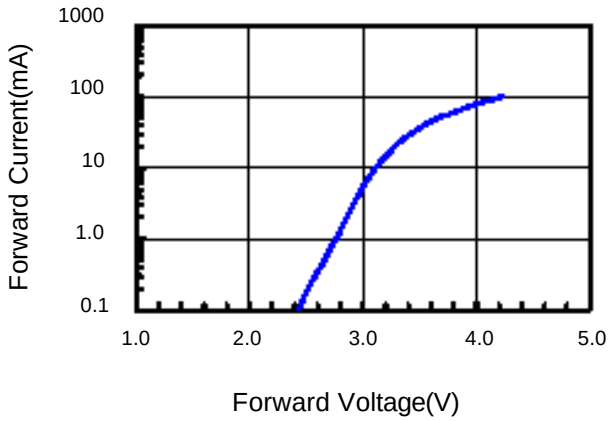


Fig.2 Relative Intensity vs. Forward Current

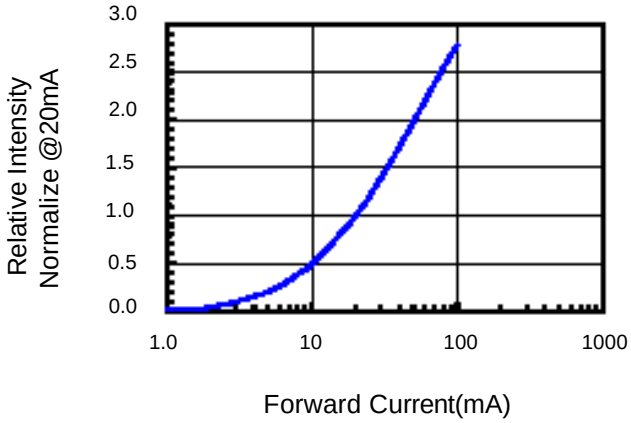


Fig.3 Forward Voltage vs. Temperature

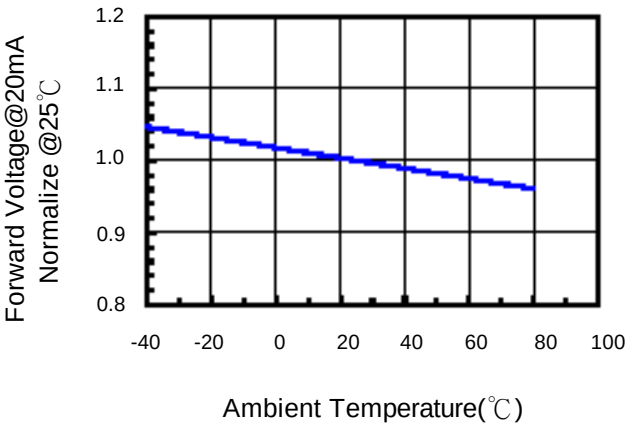


Fig.4 Relative Intensity vs. Temperature

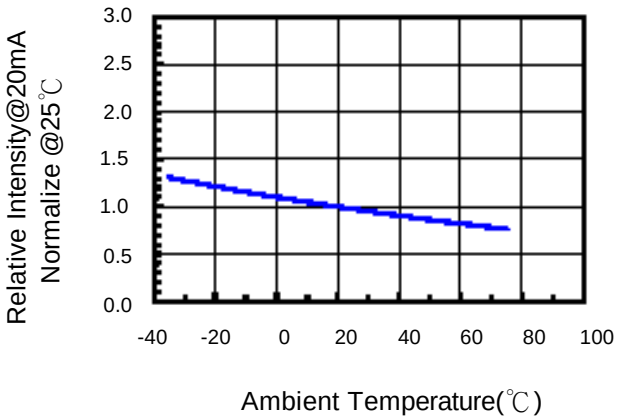


Fig.5 Relative Intensity vs. Wavelength

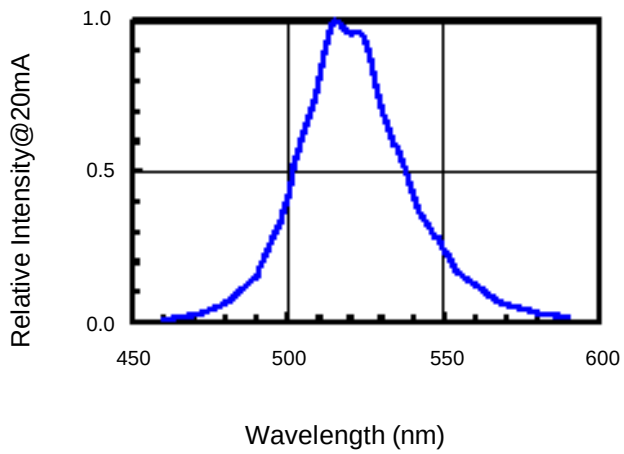
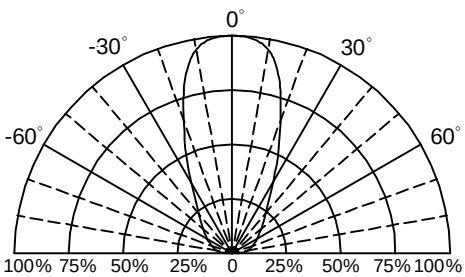


Fig.6 Directive Radiation



Typical Electro-Optical Characteristics Curve

DBK CHIP

Fig.1 Forward current vs. Forward Voltage

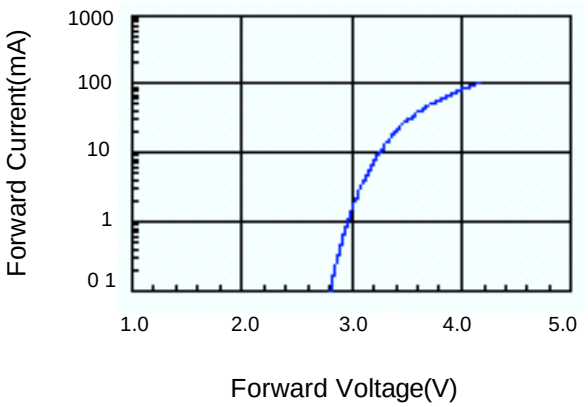


Fig.2 Relative Intensity vs. Forward Current

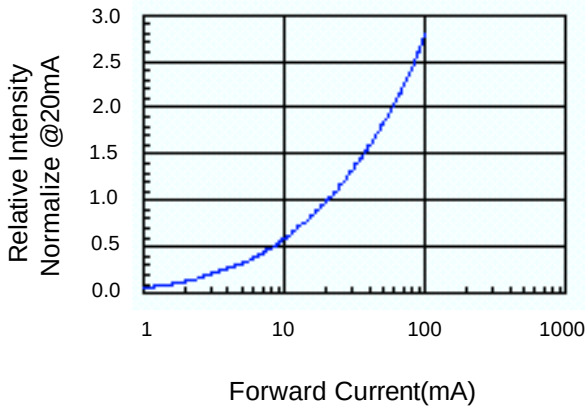


Fig.3 Forward Voltage vs. Temperature

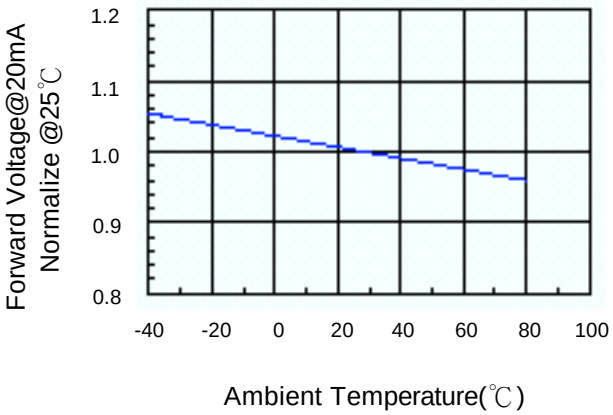


Fig.4 Relative Intensity vs. Temperature

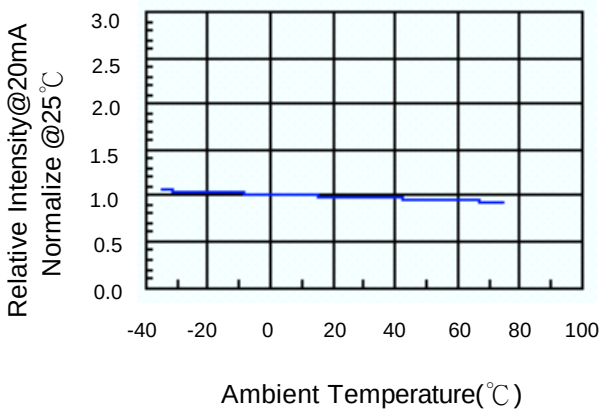


Fig.5 Relative Intensity vs. Wavelength

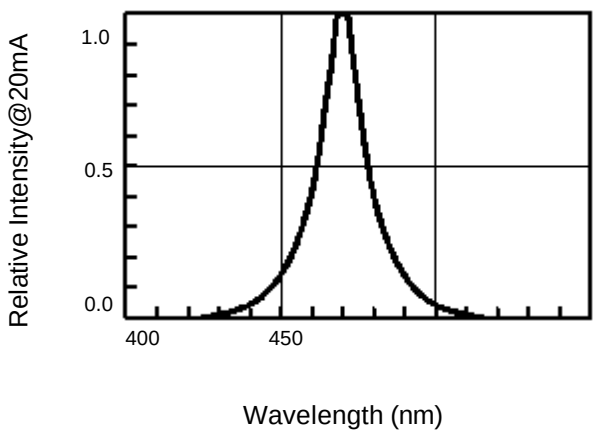
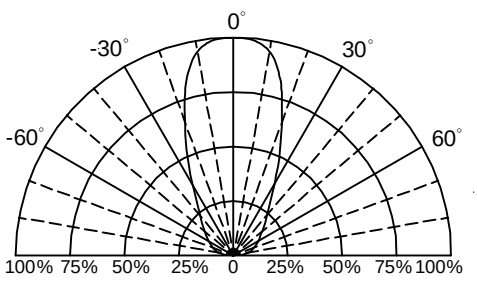


Fig.6 Directive Radiation



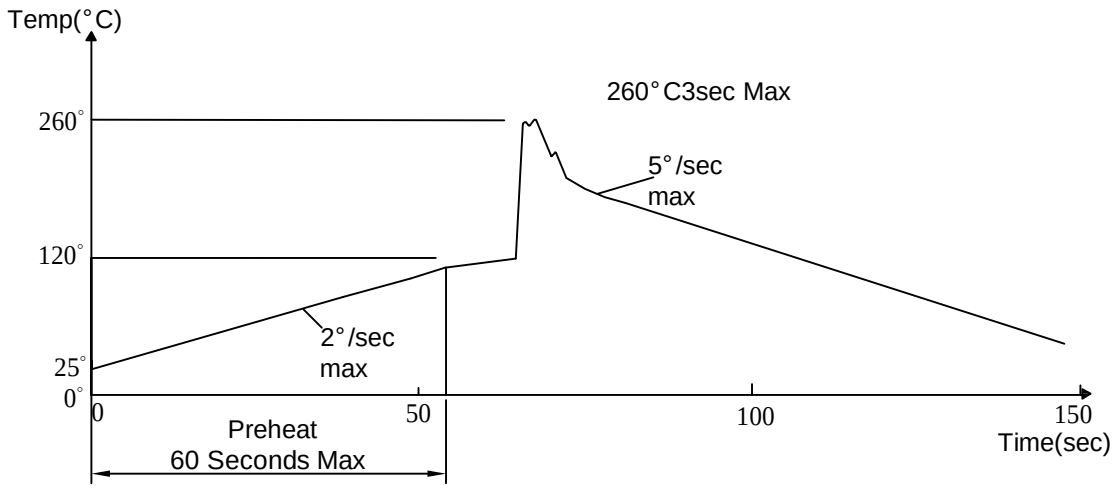
Soldering Condition(Pb-Free)

1.Iron:

Soldering Iron:30W Max
Temperature 350°C Max
Soldering Time:3 Seconds Max(One time only)
Distance:2mm Min(From solder joint to body)

2.Wave Soldering Profile

Dip Soldering
Preheat: 120°C Max
Preheat time: 60seconds Max
Ramp-up
2°C/sec(max)
Ramp-Down:-5°C/sec(max)
Solder Bath:260°C Max
Dipping Time:3 seconds Max
Distance:2mm Min(From solder joint to body)



Note: 1.Wave solder should not be made more than one time.
2.You can just only select one of the soldering conditions as above.

Reliability Test:

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=20mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of detemining the resistance of a part in electrical and themal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105℃±5℃ 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40℃±5℃ 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65℃±5℃ 2.RH=90％~95％ 3.t=240hrs±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105℃±5℃&-40℃±5℃ (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260℃±5℃ 2.Dwell time= 10±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230℃±5℃ 2.Dwell time=5±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2